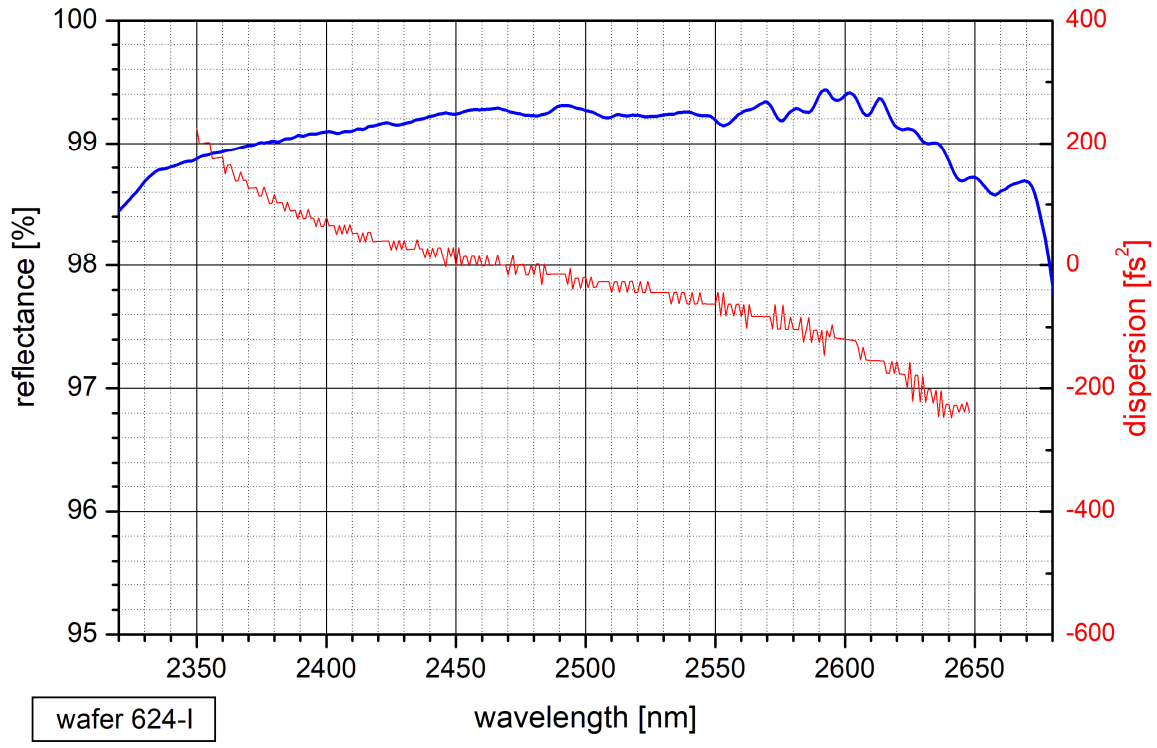
SAM™ Data Sheet SAM-2400-1-10ps-x, λ = 2400 nm

Laser wavelength	λ = 2400 nm
High reflection band	λ = 2300 .. 2650 nm
Absorbance	A_0 = 1 %
Modulation depth	ΔR = 0.6 %
Non-saturable loss	A_{ns} = 0.4 %
Saturation fluence	Φ_{sat} = 90 µJ/cm^2
Relaxation time constant	τ ~ 10 ps
Damage threshold	Φ = 1.5 mJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	620 µm
Protection	the SAM is protected with a dielectric AR layer
Reverse design	the absorber layer is illuminated through the 620 µm thick GaAs wafer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a copper heat sink with 12.7 mm diameter
x = 25.4 g	glued on a copper heat sink with 25.4 mm diameter
x = 12.7 s	soldered on a copper heat sink with 12.7 mm diameter
x = 25.4 s	soldered on a copper heat sink with 25.4 mm diameter
x = 25.0 w	soldered on a water cooled copper heat sink with 25.0 mm diameter

Low intensity spectral reflectance



Reverse design of the SAM-2400-1-x-500fs